

# BRCS120N06SRA

Rev.A Apr.-2023

## / Descriptions

N TO-220

N-CHANNEL MOSFET in a TO-220 Plastic Package.

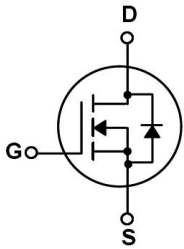
## / Features

Low  $R_{DS(on)}$ , low gate charge, low  $C_{rss}$ , fast switching, HF Product.

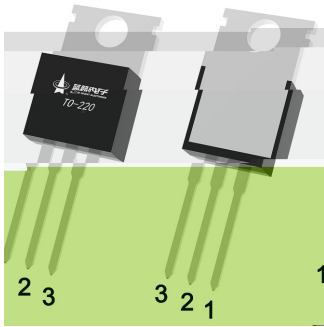
## / Applications

Suited for low voltage applications such as automotive, DC/DC Converters, and high efficiency switching for power management in portable and battery operated products.

## / Equivalent Circuit



## / Pinning



PIN1 G

PIN 2 D

PIN 3 S

## / Marking

See Marking Instructions.

## / Absolute Maximum Ratings(Ta=25 )

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V <sub>DSS</sub>	60	V
Drain Current	I <sub>D</sub> (Tc=25 )	60	A
Drain Current - Pulsed	I <sub>DM</sub>	225	A
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Avalanche Current	I <sub>AS</sub>	20	A
Single Pulsed Avalanche Energy	E <sub>AS</sub>	170	mJ
Power Dissipation	P <sub>D</sub> (Tc=25 )	96	W
Storage Temperature Range	T <sub>stg</sub>	-55 150	
Thermal Resistance-Junction to Ambient	t 10s	R <sub>JA</sub>	15
	Steady-State		62
Thermal Resistance-Junction to Case	Steady-State	R <sub>JC</sub>	1.3

## / Electrical Characteristics(Ta=25 )

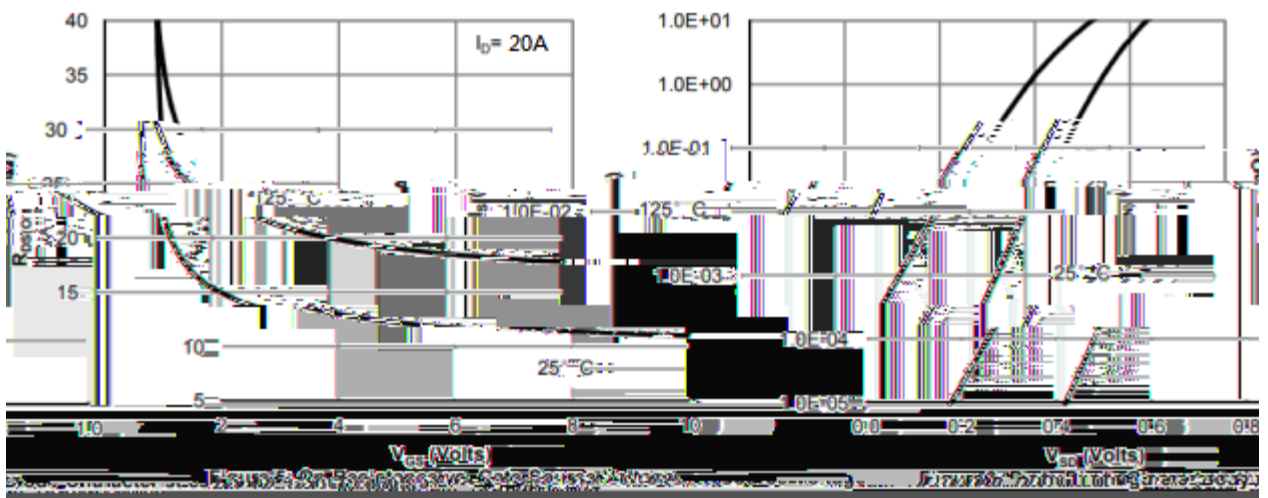
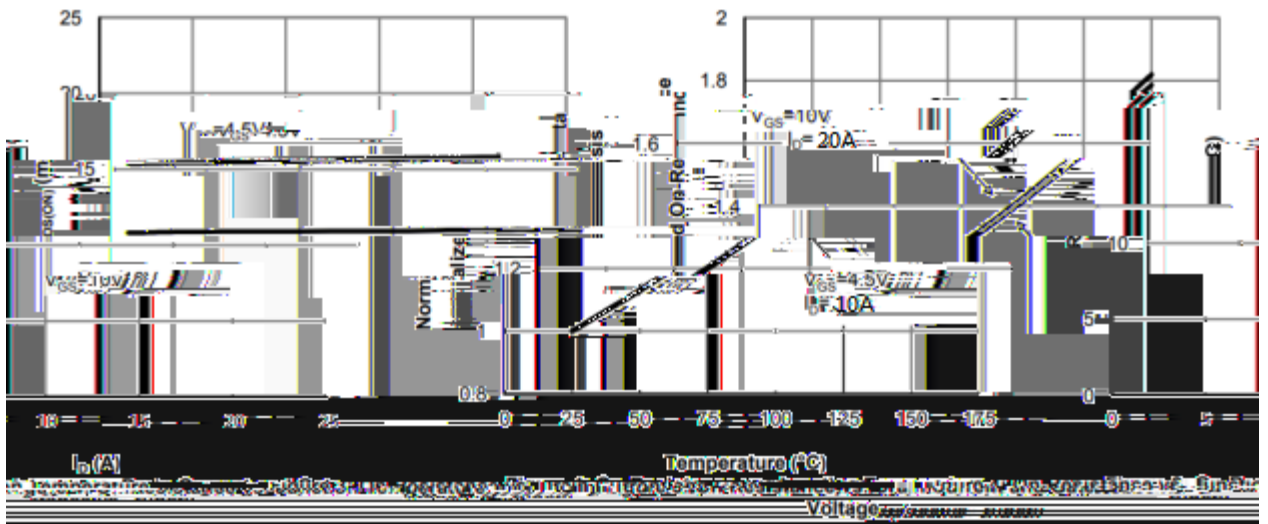
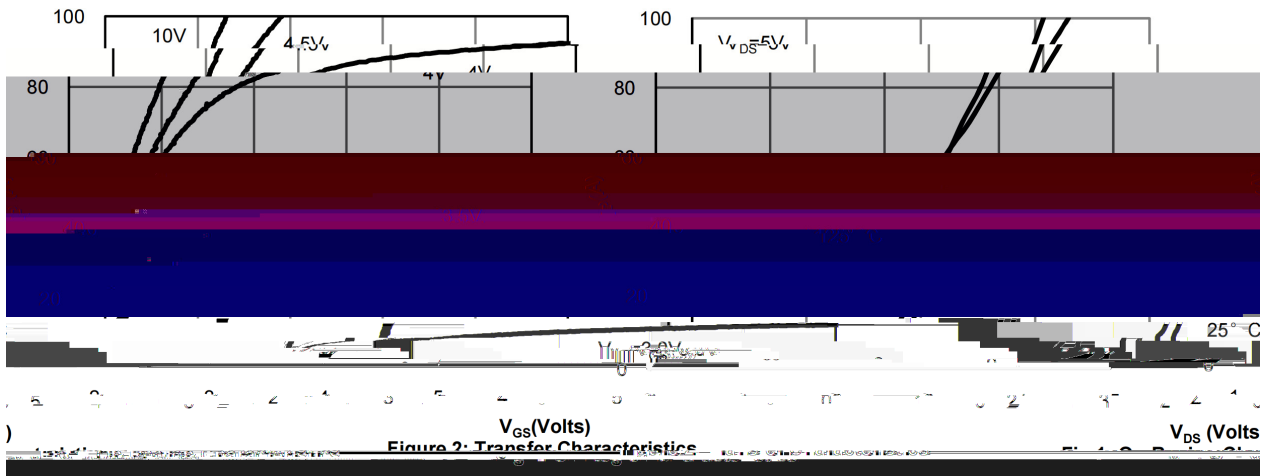
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	60	63		V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V V <sub>GS</sub> =0V			1.0	μA
		V <sub>DS</sub> =48V T <sub>C</sub> =150			10	
Gate-Body Leakage Current Forward	I <sub>GSS</sub>	V <sub>GS</sub> =±20V V <sub>DS</sub> =0V			±0.1	μA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> I <sub>D</sub> =250μA	1	1.6	3	V
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V I <sub>D</sub> =25A		10.5	15	m
		V <sub>GS</sub> =4.5V I <sub>D</sub> =18A		13.5	20	
Drain-Source Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V I <sub>S</sub> =25A			1.25	V
Gate resistance	R <sub>g</sub>	V <sub>GS</sub> =0V V <sub>DS</sub> =0V, f=1MHz		1.49		
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =25V V <sub>GS</sub> =0V f=1.0MHz		1010		pF
Output Capacitance	C <sub>oss</sub>			250		
Reverse Transfer Capacitance	C <sub>rss</sub>			280		
Total Gate Charge	Q <sub>g</sub> (10V)	V <sub>GS</sub> =10V V <sub>DS</sub> =30V I <sub>D</sub> =20A		22		nC
Total Gate Charge	Q <sub>g</sub> (4.5V)			8.7		
Gate Source Charge	Q <sub>gs</sub>			5.5		
Gate Drain Charge	Q <sub>gd</sub>			2.6		

# BRCS120N06SRA

Rev.A Apr.-2023

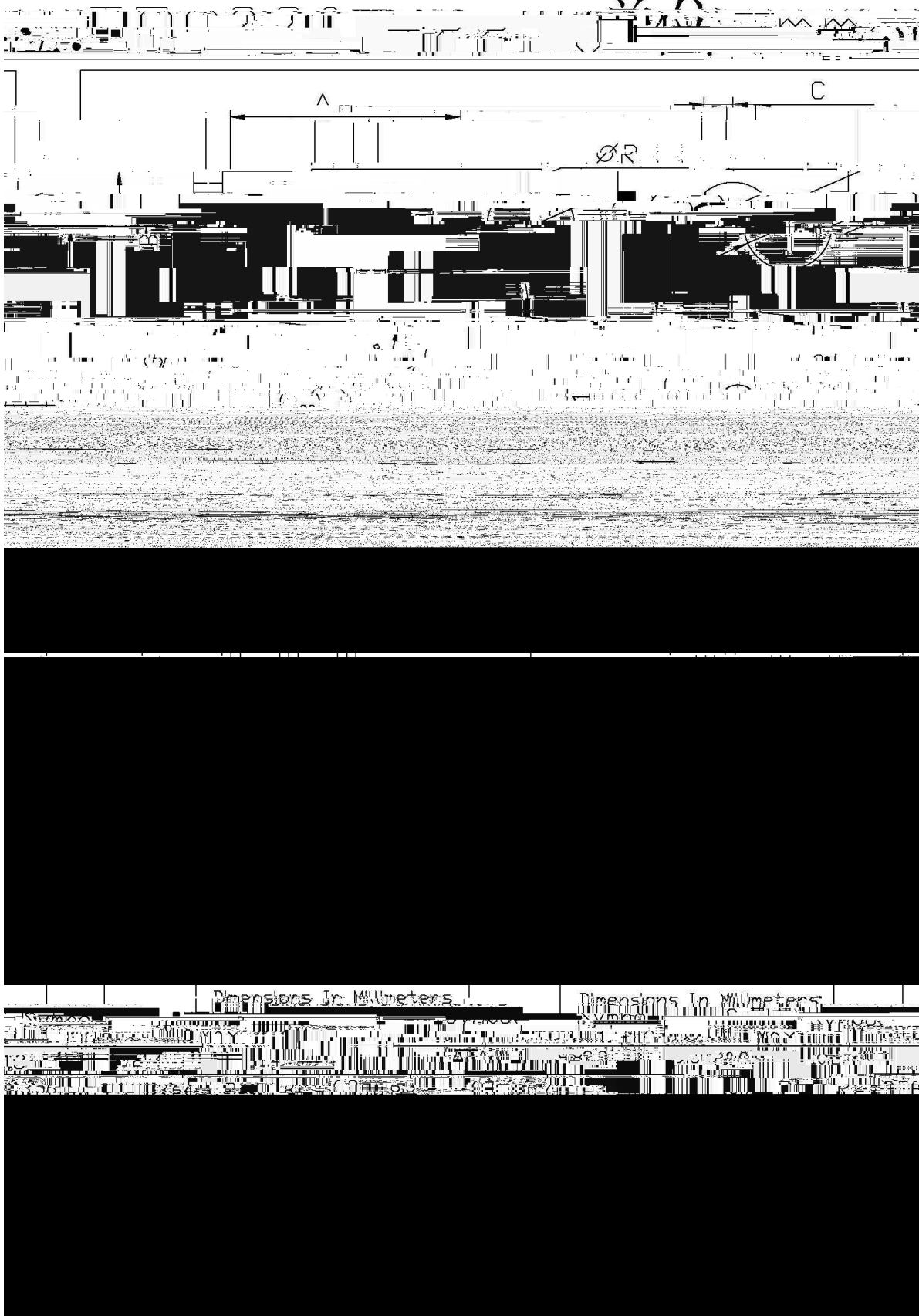
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=10V$ $V_{DS}=30V$ $R_L=1.5$ $R_{GEN}=3$		8.9		ns
Turn-On Rise Time	$t_r$			3.7		
Turn-Off Delay Time	$t_{d(off)}$			25		
Turn-Off Fall Time	$t_f$					

/ Electrical Characteristic Curve

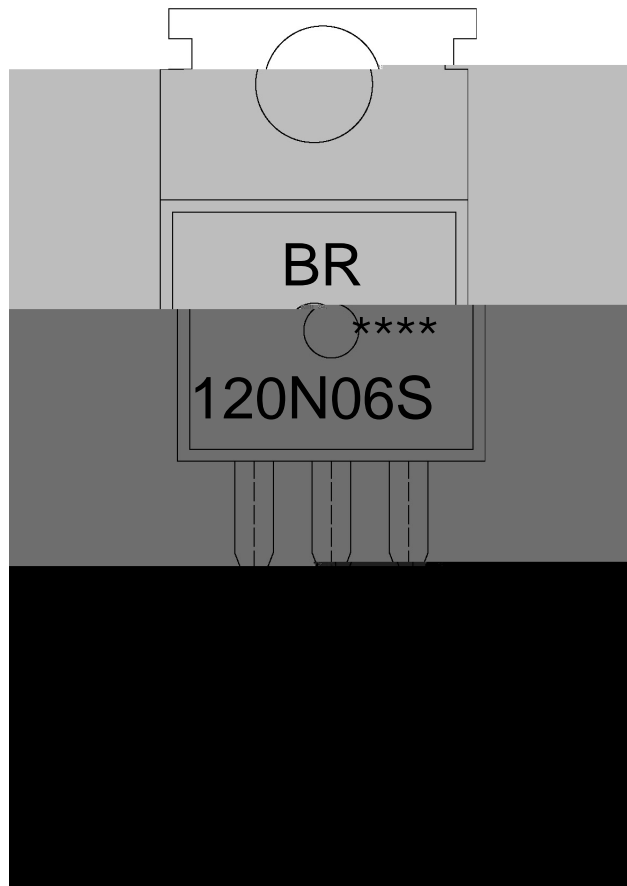


**BRCS120N06SRA**  
Rev.A Apr.-2023

**/ Package Dimensions**



**/ Marking Instructions**



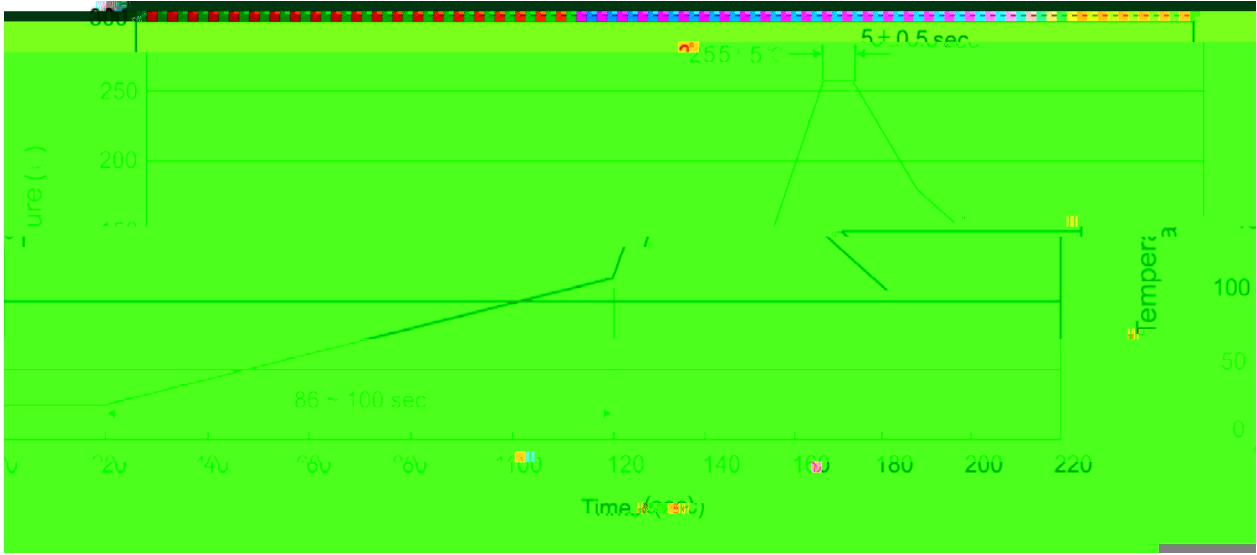
Note:

BR: Company Code

120N06S: Product Type

\*\*\*\*: Lot No. Code, code change with Lot No

( ) / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- |   |     |     |    |          |   |
|---|-----|-----|----|----------|---|
| 1 | 25  | 150 | 60 | 90sec;   | 1.Preheating:25~150 , Time:60~90sec.    |
| 2 | 255 | 5   | 5  | 0.5sec;  | 2.Peak Temp.:255 5 , Duration:5 0.5sec. |
| 3 |     |     | 2  | 10 /sec. | 3. Cooling Speed: 2~10 /sec.            |

/ Resistance to Soldering Heat Test Conditions

270 ± 5                      10 ± 1 sec.                      Temp.:270±5                      Time:10±1 sec

/ Packaging SPEC.

" á ô % ^ / B U Y K " 3 1 € Ò " Œ